(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
16 November 2006 (16.11.2006)

PCT

(10) International Publication Number
WO 2006/122119 A3

(51) International Patent Classification:
*H01L 21/461* (2006.01)

(21) International Application Number:
PCT/US2006/017917

(22) International Filing Date: 8 May 2006 (08.05.2006)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
11/126,648 10 May 2005 (10.05.2005) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

**Published:**
— *with international search report*
— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report:
21 June 2007

*For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.*

WO 2006/122119 A3

(54) Title: METHOD FOR RESIST STRIP IN PRESENCE OF REGULAR LOW K AND/OR POROUS LOW K DIELECTRIC MATERIALS

(57) Abstract: A two-step process is disclosed for stripping photoresist material from a substrate, wherein the substrate includes a low k dielectric material underlying the photoresist material and a polymer film overlying both the photoresist material and the low k dielectric material. The first step of the two-step process uses an oxygen plasma to remove the polymer film. The second step of the two-step process uses an ammonia plasma to remove the photoresist material, wherein the second step commences after completion of the first step. Each step of the two-step photoresist stripping process is respectively defined by particular values for process parameters including chemistry, temperature, pressure, gas flow rate, radio frequency power and frequency, and duration.